



#### Welcome to E-XFL.COM

#### What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

#### Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

#### Details

Product Status	Discontinued at Digi-Key
Core Processor	ARM® Cortex®-M0+
Core Size	32-Bit Single-Core
Speed	25MHz
Connectivity	I <sup>2</sup> C, IrDA, SmartCard, SPI, UART/USART, USB
Peripherals	Brown-out Detect/Reset, DMA, I <sup>2</sup> S, POR, PWM, WDT
Number of I/O	15
Program Memory Size	32KB (32K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	8K x 8
Voltage - Supply (Vcc/Vdd)	1.98V ~ 3.8V
Data Converters	A/D 4x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	24-VQFN Exposed Pad
Supplier Device Package	24-QFN (5x5)
Purchase URL	https://www.e-xfl.com/product-detail/silicon-labs/efm32hg309f32g-b-qfn24

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

# **2 System Summary**

# 2.1 System Introduction

The EFM32 MCUs are the world's most energy friendly microcontrollers. With a unique combination of the powerful 32-bit ARM Cortex-M0+, innovative low energy techniques, short wake-up time from energy saving modes, and a wide selection of peripherals, the EFM32HG microcontroller is well suited for any battery operated application as well as other systems requiring high performance and low-energy consumption. This section gives a short introduction to each of the modules in general terms and also shows a summary of the configuration for the EFM32HG309 devices. For a complete feature set and in-depth information on the modules, the reader is referred to the *EFM32HG Reference Manual*.

A block diagram of the EFM32HG309 is shown in Figure 2.1 (p. 3).



#### Figure 2.1. Block Diagram

# 2.1.1 ARM Cortex-M0+ Core

The ARM Cortex-M0+ includes a 32-bit RISC processor which can achieve as much as 0.9 Dhrystone MIPS/MHz. A Wake-up Interrupt Controller handling interrupts triggered while the CPU is asleep is included as well. The EFM32 implementation of the Cortex-M0+ is described in detail in *ARM Cortex-M0+ Devices Generic User Guide*.

# 2.1.2 Debug Interface (DBG)

This device includes hardware debug support through a 2-pin serial-wire debug interface and a Micro Trace Buffer (MTB) for data/instruction tracing.

# 2.1.3 Memory System Controller (MSC)

The Memory System Controller (MSC) is the program memory unit of the EFM32HG microcontroller. The flash memory is readable and writable from both the Cortex-M0+ and DMA. The flash memory is divided into two blocks; the main block and the information block. Program code is normally written to the main block. Additionally, the information block is available for special user data and flash lock bits.

Slave arbitration and timeouts are also provided to allow implementation of an SMBus compliant system. The interface provided to software by the I<sup>2</sup>C module, allows both fine-grained control of the transmission process and close to automatic transfers. Automatic recognition of slave addresses is provided in all energy modes.

# 2.1.12 Universal Synchronous/Asynchronous Receiver/Transmitter (US-ART)

The Universal Synchronous Asynchronous serial Receiver and Transmitter (USART) is a very flexible serial I/O module. It supports full duplex asynchronous UART communication as well as RS-485, SPI, MicroWire and 3-wire. It can also interface with ISO7816 SmartCards, IrDA and I2S devices.

# 2.1.13 Pre-Programmed USB/UART Bootloader

The bootloader presented in application note AN0042 is pre-programmed in the device at factory. The bootloader enables users to program the EFM32 through a UART or a USB CDC class virtual UART without the need for a debugger. The autobaud feature, interface and commands are described further in the application note.

# 2.1.14 Low Energy Universal Asynchronous Receiver/Transmitter (LEUART)

The unique LEUART<sup>TM</sup>, the Low Energy UART, is a UART that allows two-way UART communication on a strict power budget. Only a 32.768 kHz clock is needed to allow UART communication up to 9600 baud/s. The LEUART includes all necessary hardware support to make asynchronous serial communication possible with minimum of software intervention and energy consumption.

# 2.1.15 Timer/Counter (TIMER)

The 16-bit general purpose Timer has 3 compare/capture channels for input capture and compare/Pulse-Width Modulation (PWM) output. TIMER0 also includes a Dead-Time Insertion module suitable for motor control applications.

# 2.1.16 Real Time Counter (RTC)

The Real Time Counter (RTC) contains a 24-bit counter and is clocked either by a 32.768 kHz crystal oscillator, or a 32.768 kHz RC oscillator. In addition to energy modes EM0 and EM1, the RTC is also available in EM2. This makes it ideal for keeping track of time since the RTC is enabled in EM2 where most of the device is powered down.

# 2.1.17 Pulse Counter (PCNT)

The Pulse Counter (PCNT) can be used for counting pulses on a single input or to decode quadrature encoded inputs. It runs off either the internal LFACLK or the PCNTn\_S0IN pin as external clock source. The module may operate in energy mode EM0 - EM3.

# 2.1.18 Analog Comparator (ACMP)

The Analog Comparator is used to compare the voltage of two analog inputs, with a digital output indicating which input voltage is higher. Inputs can either be one of the selectable internal references or from external pins. Response time and thereby also the current consumption can be configured by altering the current supply to the comparator.

# 2.1.19 Voltage Comparator (VCMP)

The Voltage Supply Comparator is used to monitor the supply voltage from software. An interrupt can be generated when the supply falls below or rises above a programmable threshold. Response time and thereby also the current consumption can be configured by altering the current supply to the comparator.

# 2.1.20 Analog to Digital Converter (ADC)

The ADC is a Successive Approximation Register (SAR) architecture, with a resolution of up to 12 bits at up to one million samples per second. The integrated input mux can select inputs from 2 external pins and 6 internal signals.

### 2.1.21 Current Digital to Analog Converter (IDAC)

The current digital to analog converter can source or sink a configurable constant current, which can be output on, or sinked from pin or ADC. The current is configurable with several ranges of various step sizes.

# 2.1.22 Advanced Encryption Standard Accelerator (AES)

The AES accelerator performs AES encryption and decryption with 128-bit. Encrypting or decrypting one 128-bit data block takes 52 HFCORECLK cycles with 128-bit keys. The AES module is an AHB slave which enables efficient access to the data and key registers. All write accesses to the AES module must be 32-bit operations, i.e. 8- or 16-bit operations are not supported.

### 2.1.23 General Purpose Input/Output (GPIO)

In the EFM32HG309, there are 15 General Purpose Input/Output (GPIO) pins, which are divided into ports with up to 16 pins each. These pins can individually be configured as either an output or input. More advanced configurations like open-drain, filtering and drive strength can also be configured individually for the pins. The GPIO pins can also be overridden by peripheral pin connections, like Timer PWM outputs or USART communication, which can be routed to several locations on the device. The GPIO supports up to 10 asynchronous external pin interrupts, which enables interrupts from any pin on the device. Also, the input value of a pin can be routed through the Peripheral Reflex System to other peripherals.

# **2.2 Configuration Summary**

The features of the EFM32HG309 is a subset of the feature set described in the EFM32HG Reference Manual. Table 2.1 (p. 6) describes device specific implementation of the features.

Module	Configuration	Pin Connections
Cortex-M0+	Full configuration	NA
DBG	Full configuration	DBG_SWCLK, DBG_SWDIO,
MSC	Full configuration	NA
DMA	Full configuration	NA
RMU	Full configuration	NA
EMU	Full configuration	NA
СМИ	Full configuration	CMU_OUT0, CMU_OUT1
WDOG	Full configuration	NA
PRS	Full configuration	NA
USB	Full configuration	USB_VREGI, USB_VREGO, USB_DM, USB_DMPU, USB_DP
I2C0	Full configuration	I2C0_SDA, I2C0_SCL
USART0	Full configuration with IrDA and I2S	US0_TX, US0_RX. US0_CLK, US0_CS
USART1	Full configuration with I2S and IrDA	US1_TX, US1_RX, US1_CLK, US1_CS

Table 2.1. Configuration	Summary
--------------------------	---------



Symbol	Parameter	Condition	Min	Тур	Мах	Unit
	Parameter     Image: Constraint of the second state of the second	24 MHz HFXO, all peripheral clocks disabled, V <sub>DD</sub> = 3.0 V, $T_{AMB}$ =25°C		64	68	μΑ/ MHz
		24 MHz HFXO, all peripheral clocks disabled, $V_{DD}$ = 3.0 V, $T_{AMB}$ =85°C		67	71	μΑ/ MHz
		24 MHz USHFRCO, all peripheral clocks disabled, $V_{DD}$ = 3.0 V, $T_{AMB}$ =25°C		85	91	μΑ/ MHz
		24 MHz USHFRCO, all peripheral clocks disabled, $V_{DD}$ = 3.0 V, $T_{AMB}$ =85°C		86	92	μΑ/ MHz
		24 MHz HFRCO, all peripheral clocks disabled, $V_{DD}$ = 3.0 V, $T_{AMB}$ =25°C		51	55	μΑ/ MHz
		24 MHz HFRCO, all peripheral clocks disabled, $V_{DD}$ = 3.0 V, $T_{AMB}$ =85°C		52	56	μΑ/ MHz
	EM1 current	21 MHz HFRCO, all peripheral clocks disabled, $V_{DD}$ = 3.0 V, $T_{AMB}$ =25°C		53	57	μΑ/ MHz
1-1-1		21 MHz HFRCO, all peripheral clocks disabled, $V_{DD}$ = 3.0 V, $T_{AMB}$ =85°C		54	58	µA/ MHz
'EM1		14 MHz HFRCO, all peripheral clocks disabled, $V_{DD}$ = 3.0 V, $T_{AMB}$ =25°C		56	59	μΑ/ MHz
		14 MHz HFRCO, all peripheral clocks disabled, $V_{DD}$ = 3.0 V, $T_{AMB}$ =85°C		57	61	μΑ/ MHz
		11 MHz HFRCO, all peripheral clocks disabled, $V_{DD}$ = 3.0 V, $T_{AMB}$ =25°C		58	61	μΑ/ MHz
		11 MHz HFRCO, all peripheral clocks disabled, $V_{DD}$ = 3.0 V, $T_{AMB}$ =85°C		59	63	µA/ MHz
		6.6 MHz HFRCO, all peripher- al clocks disabled, $V_{DD}$ = 3.0 V, $T_{AMB}$ =25°C		64	68	μΑ/ MHz
		6.6 MHz HFRCO, all peripheral clocks disabled, $V_{DD}$ = 3.0 V, $T_{AMB}$ =85°C		67	71	μΑ/ MHz
		1.2 MHz HFRCO. all peripheral clocks disabled, $V_{DD}$ = 3.0 V, $T_{AMB}$ =25°C		106	114	µA/ MHz
		1.2 MHz HFRCO. all peripher- al clocks disabled, $V_{DD}$ = 3.0 V, $T_{AMB}$ =85°C		114	126	µA/ MHz
I <sub>EM2</sub>	EM2 current	EM2 current with RTC prescaled to 1 Hz, 32.768 kHz LFRCO, $V_{DD}$ = 3.0 V, $T_{AMB}$ =25°C		0.9	1.35	μΑ

*Figure 3.3. EM0 Current consumption while executing prime number calculation code from flash with HFRCO running at 14 MHz* 



*Figure 3.4. EM0 Current consumption while executing prime number calculation code from flash with HFRCO running at 11 MHz* 



### 3.4.3 EM2 Current Consumption

Figure 3.11. EM2 current consumption. RTC prescaled to 1kHz, 32.768 kHz LFRCO.





# 3.4.4 EM3 Current Consumption

Figure 3.12. EM3 current consumption.



### 3.4.5 EM4 Current Consumption

Figure 3.13. EM4 current consumption.



# 3.5 Transition between Energy Modes

The transition times are measured from the trigger to the first clock edge in the CPU.

Table 3.4. Energy Modes Transitions

Symbol	Parameter	Min	Тур	Max	Unit
t <sub>EM10</sub>	Transition time from EM1 to EM0		0		HF- CORE- CLK cycles
t <sub>EM20</sub>	Transition time from EM2 to EM0		2		μs
t <sub>EM30</sub>	Transition time from EM3 to EM0		2		μs
t <sub>EM40</sub>	Transition time from EM4 to EM0		163		μs

# 3.6 Power Management

The EFM32HG requires the AVDD\_x, VDD\_DREG and IOVDD\_x pins to be connected together (with optional filter) at the PCB level. For practical schematic recommendations, please see the application note, "AN0002 EFM32 Hardware Design Considerations".

#### Table 3.5. Power Management

Symbol	Parameter	Condition	Min	Тур	Max	Unit
	BOD threshold on	EMO	1.74		1.96	V
VBODextthr-	ply voltage	EM2	1.71	1.86	1.98	V
V <sub>BODextthr+</sub>	BOD threshold on rising external sup- ply voltage			1.85		V
t <sub>RESET</sub>	Delay from reset is released until program execution starts	Applies to Power-on Reset, Brown-out Reset and pin reset.		163		μs
C <sub>DECOUPLE</sub>	Voltage regulator decoupling capaci- tor.	X5R capacitor recommended. Apply between DECOUPLE pin and GROUND		1		μF
C <sub>USB_VREGO</sub>	USB voltage regu- lator out decoupling capacitor.	X5R capacitor recommended. Apply between USB_VREGO pin and GROUND		1		μF
C <sub>USB_VREGI</sub>	USB voltage regula- tor in decoupling ca- pacitor.	X5R capacitor recommended. Apply between USB_VREGI pin and GROUND		4.7		μF

# 3.7 Flash

#### Table 3.6. Flash

Symbol	Parameter	Condition	Min	Тур	Мах	Unit
EC <sub>FLASH</sub>	Flash erase cycles before failure		20000			cycles
		T <sub>AMB</sub> <150°C	10000			h
RET <sub>FLASH</sub>	Flash data retention	T <sub>AMB</sub> <85°C	10			years
		T <sub>AMB</sub> <70°C	20			years
tw_prog	Word (32-bit) pro- gramming time		20			μs
t <sub>P_ERASE</sub>	Page erase time		20	20.4	20.8	ms
t <sub>D_ERASE</sub>	Device erase time		40	40.8	41.6	ms
I <sub>ERASE</sub>	Erase current				7 <sup>1</sup>	mA
I <sub>WRITE</sub>	Write current				7 <sup>1</sup>	mA
V <sub>FLASH</sub>	Supply voltage dur- ing flash erase and write		1.98		3.8	V

<sup>1</sup>Measured at 25°C

# **3.8 General Purpose Input Output**

#### Table 3.7. GPIO

Symbol	Parameter	Condition	Min	Тур	Мах	Unit
V <sub>IOIL</sub>	Input low voltage				0.30V <sub>DD</sub>	V
V <sub>IOIH</sub>	Input high voltage		0.70V <sub>DD</sub>			V



Symbol	Parameter	Condition	Min	Тур	Мах	Unit
Symbol		Sourcing 0.1 mA, V <sub>DD</sub> =1.98 V, GPIO_Px_CTRL DRIVEMODE = LOWEST		0.80V <sub>DD</sub>		V
		Sourcing 0.1 mA, V <sub>DD</sub> =3.0 V, GPIO_Px_CTRL DRIVEMODE = LOWEST		0.90V <sub>DD</sub>		V
		Sourcing 1 mA, V <sub>DD</sub> =1.98 V, GPIO_Px_CTRL DRIVEMODE = LOW		0.85V <sub>DD</sub>		V
Vices	Output high volt- age (Production test	Sourcing 1 mA, V <sub>DD</sub> =3.0 V, GPIO_Px_CTRL DRIVEMODE = LOW		0.90V <sub>DD</sub>		V
VIOOH	condition = 3.0V, DRIVEMODE = STANDARD)	Sourcing 6 mA, V <sub>DD</sub> =1.98 V, GPIO_Px_CTRL DRIVEMODE = STANDARD	0.75V <sub>DD</sub>			V
		Sourcing 6 mA, V <sub>DD</sub> =3.0 V, GPIO_Px_CTRL DRIVEMODE = STANDARD	0.85V <sub>DD</sub>			V
		Sourcing 20 mA, V <sub>DD</sub> =1.98 V, GPIO_Px_CTRL DRIVEMODE = HIGH	0.60V <sub>DD</sub>			V
		Sourcing 20 mA, V <sub>DD</sub> =3.0 V, GPIO_Px_CTRL DRIVEMODE = HIGH	0.80V <sub>DD</sub>			V
	Output low voltage (Production test	Sinking 0.1 mA, V <sub>DD</sub> =1.98 V, GPIO_Px_CTRL DRIVEMODE = LOWEST		0.20V <sub>DD</sub>		V
		Sinking 0.1 mA, V <sub>DD</sub> =3.0 V, GPIO_Px_CTRL DRIVEMODE = LOWEST		0.10V <sub>DD</sub>		V
		Sinking 1 mA, V <sub>DD</sub> =1.98 V, GPIO_Px_CTRL DRIVEMODE = LOW		0.10V <sub>DD</sub>		V
Vice		Sinking 1 mA, V <sub>DD</sub> =3.0 V, GPIO_Px_CTRL DRIVEMODE = LOW		0.05V <sub>DD</sub>		V
VIOOL	DRIVEMODE = STANDARD)	Sinking 6 mA, V <sub>DD</sub> =1.98 V, GPIO_Px_CTRL DRIVEMODE = STANDARD			0.30V <sub>DD</sub>	V
		Sinking 6 mA, V <sub>DD</sub> =3.0 V, GPIO_Px_CTRL DRIVEMODE = STANDARD			0.20V <sub>DD</sub>	V
		Sinking 20 mA, V <sub>DD</sub> =1.98 V, GPIO_Px_CTRL DRIVEMODE = HIGH			0.35V <sub>DD</sub>	V
Viooh Viool Viool Iioleak Rpu		Sinking 20 mA, V <sub>DD</sub> =3.0 V, GPIO_Px_CTRL DRIVEMODE = HIGH			0.25V <sub>DD</sub>	V
I <sub>IOLEAK</sub>	Input leakage cur- rent	High Impedance IO connected to GROUND or Vdd		±0.1	±40	nA
R <sub>PU</sub>	I/O pin pull-up resis- tor			40		kOhm



#### ...the world's most energy friendly microcontrollers

Symbol	Parameter	Condition	Min	Тур	Max	Unit
R <sub>PD</sub>	I/O pin pull-down re- sistor			40		kOhm
R <sub>IOESD</sub>	Internal ESD series resistor			200		Ohm
t <sub>IOGLITCH</sub>	Pulse width of puls- es to be removed by the glitch sup- pression filter		10		50	ns
t	Output fall time	GPIO_Px_CTRL DRIVEMODE = LOWEST and load capaci- tance $C_L$ =12.5-25pF.	20+0.1C <sub>L</sub>		250	ns
t <sub>ioof</sub>		GPIO_Px_CTRL DRIVEMODE = LOW and load capacitance $C_L$ =350-600pF	20+0.1C <sub>L</sub>		250	ns
V <sub>IOHYST</sub>	I/O pin hysteresis (V <sub>IOTHR+</sub> - V <sub>IOTHR-</sub> )	V <sub>DD</sub> = 1.98 - 3.8 V	0.1V <sub>DD</sub>			V



### Figure 3.14. Typical Low-Level Output Current, 2V Supply Voltage



GPIO\_Px\_CTRL DRIVEMODE = LOWEST



GPIO\_Px\_CTRL DRIVEMODE = STANDARD



GPIO\_Px\_CTRL DRIVEMODE = LOW



GPIO\_Px\_CTRL DRIVEMODE = HIGH

### 3.9.3 LFRCO

#### Table 3.10. LFRCO

Symbol	Parameter	Condition	Min	Тур	Мах	Unit
f <sub>LFRCO</sub>	Oscillation frequen- cy , $V_{DD}$ = 3.0 V, $T_{AMB}$ =25°C		31.3	32.768	34.3	kHz
t <sub>LFRCO</sub>	Startup time not in- cluding software calibration			150		μs
I <sub>LFRCO</sub>	Current consump- tion			361	492	nA
TUNESTEP <sub>L-</sub> FRCO	Frequency step for LSB change in TUNING value			202		Hz

Figure 3.20. Calibrated LFRCO Frequency vs Temperature and Supply Voltage







Symbol	Parameter	Condition	Min	Тур	Мах	Unit
t <sub>ADCACQVDD3</sub>	Required acquisi- tion time for VDD/3 reference		2			μs
	Startup time of ref- erence generator and ADC core in NORMAL mode			5		μs
tadcstart	Startup time of ref- erence generator and ADC core in KEEPADCWARM mode			1		μs
		1 MSamples/s, 12 bit, single ended, internal 1.25V refer- ence		59		dB
		1 MSamples/s, 12 bit, single ended, internal 2.5V reference		63		dB
		1 MSamples/s, 12 bit, single ended, V <sub>DD</sub> reference		65		dB
	Signal to Noise Ra- tio (SNR)	1 MSamples/s, 12 bit, differen- tial, internal 1.25V reference		60		dB
		1 MSamples/s, 12 bit, differen- tial, internal 2.5V reference		65		dB
		1 MSamples/s, 12 bit, differen- tial, 5V reference		54		dB
		1 MSamples/s, 12 bit, differential, $V_{DD}$ reference		67		dB
		1 MSamples/s, 12 bit, differen- tial, 2xV <sub>DD</sub> reference		69		dB
SINKADC		200 kSamples/s, 12 bit, sin- gle ended, internal 1.25V refer- ence		62		dB
		200 kSamples/s, 12 bit, single ended, internal 2.5V reference		63		dB
		200 kSamples/s, 12 bit, single ended, V <sub>DD</sub> reference		67		dB
		200 kSamples/s, 12 bit, differ- ential, internal 1.25V reference		63		dB
		200 kSamples/s, 12 bit, differ- ential, internal 2.5V reference		66		dB
		200 kSamples/s, 12 bit, differ- ential, 5V reference		66		dB
		200 kSamples/s, 12 bit, differ- ential, V <sub>DD</sub> reference	63	66		dB
		200 kSamples/s, 12 bit, differ- ential, 2xV <sub>DD</sub> reference		70		dB
SINAD <sub>ADC</sub>	SIgnal-to-Noise And Distortion-ratio (SINAD)	1 MSamples/s, 12 bit, single ended, internal 1.25V refer- ence		58		dB

#### Figure 3.29. ADC Integral Linearity Error vs Code, Vdd = 3V, Temp = 25°C





2015-12-04 - EFM32HG309FXX - d0296\_Rev1.00

#### Table 3.18. IDAC Range 1 Source

Symbol	Parameter	Condition	Min	Тур	Мах	Unit
	Active current with	EM0, default settings		14.4		μA
	STEPSEL=0x10	Duty-cycled		10		nA
I <sub>0x10</sub>	Nominal IDAC out- put current with STEPSEL=0x10			3.2		μA
I <sub>STEP</sub>	Step size			0.1		μA
ID	Current drop at high impedance load	$V_{IDAC_OUT} = V_{DD} - 100mV$		0.75		%
TC <sub>IDAC</sub>	Temperature coeffi- cient	V <sub>DD</sub> = 3.0 V, STEPSEL=0x10		0.7		nA/°C
VC <sub>IDAC</sub>	Voltage coefficient	T = 25 °C, STEPSEL=0x10		38.4		nA/V

#### Table 3.19. IDAC Range 1 Sink

Symbol	Parameter	Condition	Min	Тур	Мах	Unit
I <sub>IDAC</sub>	Active current with STEPSEL=0x10	EM0, default settings		19.4		μA
I <sub>0x10</sub>	Nominal IDAC out- put current with STEPSEL=0x10			3.2		μA
I <sub>STEP</sub>	Step size			0.1		μA
ID	Current drop at high impedance load	V <sub>IDAC_OUT</sub> = 200 mV		0.32		%
TC <sub>IDAC</sub>	Temperature coeffi- cient	V <sub>DD</sub> = 3.0 V, STEPSEL=0x10		0.7		nA/°C
VC <sub>IDAC</sub>	Voltage coefficient	T = 25 °C, STEPSEL=0x10		40.9		nA/V

#### Table 3.20. IDAC Range 2 Source

Symbol	Parameter	Condition	Min	Тур	Мах	Unit
	Active current with	EM0, default settings		17.3	Мах Ц   17.3 µ   10 п   8.5 µ   0.5 µ   1.22 9   2.8 г	μA
IDAC	STEPSEL=0x10	Duty-cycled		10		nA
I <sub>0x10</sub>	Nominal IDAC out- put current with STEPSEL=0x10			8.5		μΑ
I <sub>STEP</sub>	Step size			0.5		μA
ID	Current drop at high impedance load	$V_{IDAC_OUT} = V_{DD} - 100mV$		1.22		%
TC <sub>IDAC</sub>	Temperature coeffi- cient	V <sub>DD</sub> = 3.0 V, STEPSEL=0x10		2.8		nA/°C
VC <sub>IDAC</sub>	Voltage coefficient	T = 25 °C, STEPSEL=0x10		96.6		nA/V

#### Table 3.21. IDAC Range 2 Sink

Symbol	Parameter	Condition	Min	Тур	Мах	Unit
I <sub>IDAC</sub>	Active current with STEPSEL=0x10	EM0, default settings		29.3		μA

# 3.13 Voltage Comparator (VCMP)

#### Table 3.26. VCMP

Symbol	Parameter	Condition	Min	Тур	Мах	Unit
V <sub>VCMPIN</sub>	Input voltage range			V <sub>DD</sub>		V
V <sub>VCMPCM</sub>	VCMP Common Mode voltage range	BIASPROG=0b0000 and HALFBIAS=1 in VCMPn_CTRL register BIASPROG=0b1111 and HALFBIAS=0 in VCMPn_CTRL register. LPREF=0.	V <sub>DD</sub>		V	
V <sub>VCMPCM</sub>	Active current	BIASPROG=0b0000 and HALFBIAS=1 in VCMPn_CTRL register		0.2	0.8	μA
VCMP		BIASPROG=0b1111 and HALFBIAS=0 in VCMPn_CTRL register. LPREF=0.		22	35	μA
t <sub>VCMPREF</sub>	Startup time refer- ence generator	NORMAL		10		μs
V	Offset voltage	Single ended	10 μs 10 mV	mV		
▼ VCMPOFFSET	Onset voltage	Differential		10		mV
V <sub>VCMPHYST</sub>	VCMP hysteresis			17		mV
t <sub>VCMPSTART</sub>	Startup time				10	μs

The  $V_{DD}$  trigger level can be configured by setting the TRIGLEVEL field of the VCMP\_CTRL register in accordance with the following equation:

#### VCMP Trigger Level as a Function of Level Setting

V<sub>DD Trigger Level</sub>=1.667V+0.034 ×TRIGLEVEL

# 3.14 I2C

#### Table 3.27. I2C Standard-mode (Sm)

Symbol	Parameter	Min	Тур	Max	Unit
f <sub>SCL</sub>	SCL clock frequency	0		100 <sup>1</sup>	kHz
t <sub>LOW</sub>	SCL clock low time	4.7			μs
t <sub>HIGH</sub>	SCL clock high time	4.0			μs
t <sub>SU,DAT</sub>	SDA set-up time	250			ns
t <sub>HD,DAT</sub>	SDA hold time	8		3450 <sup>2,3</sup>	ns
t <sub>SU,STA</sub>	Repeated START condition set-up time	4.7			μs
t <sub>HD,STA</sub>	(Repeated) START condition hold time	4.0			μs
t <sub>SU,STO</sub>	STOP condition set-up time	4.0			μs
t <sub>BUF</sub>	Bus free time between a STOP and START condition	4.7			μs

<sup>1</sup>For the minimum HFPERCLK frequency required in Standard-mode, see the I2C chapter in the EFM32HG Reference Manual. <sup>2</sup>The maximum SDA hold time (t<sub>HD,DAT</sub>) needs to be met only when the device does not stretch the low time of SCL (t<sub>LOW</sub>).

<sup>3</sup>When transmitting data, this number is guaranteed only when I2Cn\_CLKDIV < ((3450\*10<sup>-9</sup> [s] \* f<sub>HFPERCLK</sub> [Hz]) - 5).

(3.2)

#### Table 3.28. I2C Fast-mode (Fm)

Symbol	Parameter	Min	Тур	Мах	Unit
f <sub>SCL</sub>	SCL clock frequency	0		400 <sup>1</sup>	kHz
t <sub>LOW</sub>	SCL clock low time	1.3			μs
t <sub>HIGH</sub>	SCL clock high time	0.6			μs
t <sub>SU,DAT</sub>	SDA set-up time	100			ns
t <sub>HD,DAT</sub>	SDA hold time	8		900 <sup>2,3</sup>	ns
t <sub>SU,STA</sub>	Repeated START condition set-up time	0.6			μs
t <sub>HD,STA</sub>	(Repeated) START condition hold time	0.6			μs
t <sub>su,sто</sub>	STOP condition set-up time	0.6			μs
t <sub>BUF</sub>	Bus free time between a STOP and START condition	1.3			μs

<sup>1</sup>For the minimum HFPERCLK frequency required in Fast-mode, see the I2C chapter in the EFM32HG Reference Manual. <sup>2</sup>The maximum SDA hold time ( $t_{HD,DAT}$ ) needs to be met only when the device does not stretch the low time of SCL ( $t_{LOW}$ ). <sup>3</sup>When transmitting data, this number is guaranteed only when I2Cn\_CLKDIV < ((900\*10<sup>-9</sup> [s] \* f<sub>HFPERCLK</sub> [Hz]) - 5).

#### Table 3.29. I2C Fast-mode Plus (Fm+)

Symbol	Parameter	Min	Тур	Max	Unit
f <sub>SCL</sub>	SCL clock frequency	0		1000 <sup>1</sup>	kHz
t <sub>LOW</sub>	SCL clock low time	0.5			μs
t <sub>HIGH</sub>	SCL clock high time	0.26			μs
t <sub>SU,DAT</sub>	SDA set-up time	50			ns
t <sub>HD,DAT</sub>	SDA hold time	8			ns
t <sub>SU,STA</sub>	Repeated START condition set-up time	0.26			μs
t <sub>HD,STA</sub>	(Repeated) START condition hold time	0.26			μs
t <sub>SU,STO</sub>	STOP condition set-up time	0.26			μs
t <sub>BUF</sub>	Bus free time between a STOP and START condition	0.5			μs

<sup>1</sup>For the minimum HFPERCLK frequency required in Fast-mode Plus, see the I2C chapter in the EFM32HG Reference Manual.

# 3.15 USB

The USB hardware in the EFM32HG309 passes all tests for USB 2.0 Full Speed certification. The test report will be distributed with application note "AN0046 - USB Hardware Design Guide" when ready.

#### Table 3.30. USB

Symbol	Parameter	Condition	Min	Тур	Мах	Unit
V <sub>USBOUT</sub>	USB regulator out- put voltage		3.1	3.4	3.7	V
	USB regulator out- put current	BIASPROG=0, T <sub>AMB</sub> =25°C	55.7	79.4	104.1	mA
1		BIASPROG=1, T <sub>AMB</sub> =25°C	66.0	95.9	126.4	mA
USBOUT		BIASPROG=2, T <sub>AMB</sub> =25°C	94.6	146.5	188.1	mA
		BIASPROG=3, T <sub>AMB</sub> =25°C	80.4	128.3	176.0	mA

# **4 Pinout and Package**

#### Note

Please refer to the application note "AN0002 EFM32 Hardware Design Considerations" for guidelines on designing Printed Circuit Boards (PCB's) for the EFM32HG309.

# 4.1 Pinout

The *EFM32HG309* pinout is shown in Figure 4.1 (p. 52) and Table 4.1 (p. 52). Alternate locations are denoted by "#" followed by the location number (Multiple locations on the same pin are split with "/"). Alternate locations can be configured in the LOCATION bitfield in the \*\_ROUTE register in the module in question.

#### Figure 4.1. EFM32HG309 Pinout (top view, not to scale)



#### Table 4.1. Device Pinout

	QFN24 Pin# and Name		Pin Alternate Functio	onality / Description	
Pin #	Pin Name	Analog	Timers	Communication	Other
0	VSS	Ground.			
1	PA0		TIM0_CC1 #6 TIM0_CC0 #0/1/4 PCNT0_S0IN #4	USB_DMPU #0 US1_RX #4 LEU0_RX #4 I2C0_SDA #0	PRS_CH0 #0 PRS_CH3 #3 GPIO_EM4WU0

# **EFM<sup>®</sup>32**

#### ...the world's most energy friendly microcontrollers

Alternate			LOC	ATION				
Functionality	0	1	2	3	4	5	6	Description
PRS_CH1			PC15	PE12				Peripheral Reflex System PRS, channel 1.
PRS_CH2	PC0			PE13				Peripheral Reflex System PRS, channel 2.
PRS_CH3	PC1			PA0				Peripheral Reflex System PRS, channel 3.
TIM0_CC0	PA0	PA0			PA0	PF0		Timer 0 Capture Compare input / output channel 0.
TIM0_CC1					PC0	PF1	PA0	Timer 0 Capture Compare input / output channel 1.
TIM0_CC2					PC1	PF2	PF2	Timer 0 Capture Compare input / output channel 2.
TIM0_CDTI1		PC14					PC14	Timer 0 Complimentary Deat Time Insertion channel 1.
TIM0_CDTI2		PC15					PC15	Timer 0 Complimentary Deat Time Insertion channel 2.
TIM1_CC0				PB7				Timer 1 Capture Compare input / output channel 0.
TIM1_CC1	PC14			PB8				Timer 1 Capture Compare input / output channel 1.
TIM1_CC2	PC15	PE12		PB11				Timer 1 Capture Compare input / output channel 2.
TIM2_CC0				PF2				Timer 2 Capture Compare input / output channel 0.
TIM2_CC1				PE12				Timer 2 Capture Compare input / output channel 1.
TIM2_CC2				PE13				Timer 2 Capture Compare input / output channel 2.
US0_CLK	PE12			PC15	PB13	PB13	PE12	USART0 clock input / output.
US0_CS	PE13			PC14	PB14	PB14	PE13	USART0 chip select input / output.
								USART0 Asynchronous Receive.
US0_RX				PE12	PB8	PC1	PC1	USART0 Synchronous mode Master Input / Slave Output (MISO).
								USART0 Asynchronous Transmit.Also used as receive in- out in half duplex communication.
US0_TX				PE13	PB7	PC0	PC0	USART0 Synchronous mode Master Output / Slave Input (MOSI).
US1_CLK	PB7		PF0	PC15	PB11			USART1 clock input / output.
US1_CS	PB8		PF1	PC14	PC14	PC0		USART1 chip select input / output.
								USART1 Asynchronous Receive.
US1_RX	PC1				PA0			USART1 Synchronous mode Master Input / Slave Output (MISO).
								USART1 Asynchronous Transmit.Also used as receive in-
US1_TX	PC0				PF2	PC1		USART1 Synchronous mode Master Output / Slave Input
USB DM	PC14							USB D- pin.
USB DMPU	PA0							USB D- Pullup control.
USB DP	PC15							USB D+ pin.
USB VREGI	USB VREGI							USB Input to internal 3.3 V regulator
								USB Decoupling for internal 3.3 V USB regulator and reg-
USB_VREGO	USB_VREGO							ulator output

# 4.3 GPIO Pinout Overview

The specific GPIO pins available in *EFM32HG309* is shown in Table 4.3 (p. 56). Each GPIO port is organized as 16-bit ports indicated by letters A through F, and the individual pin on this port is indicated by a number from 15 down to 0.

# List of Figures

2.1. Block Diagram	. 3
2.2. EFM32HG309 Memory Map with largest RAM and Flash sizes	7
3.1. EM0 Current consumption while executing prime number calculation code from flash with HFRCO running at 24	
MHz	11
3.2. EM0 Current consumption while executing prime number calculation code from flash with HFRCO running at 21	
MHz	11
3.3. EM0 Current consumption while executing prime number calculation code from flash with HERCO running at 14	
MHz	12
3.4 EM0 Current consumption while executing prime number calculation code from flash with HERCO running at 11	
MHz	12
3.5 EM0 Current consumption while executing prime number calculation code from flash with HERCO running at 6.6	
MHz	13
3.6 EM1 Current consumption with all peripheral clocks disabled and HERCO running at 24 MHz	13
3.7 EM1 Current consumption with all peripheral clocks disabled and HERCO running at 21 MHz	14
3.8 EM1 Current consumption with all peripheral clocks disabled and HEPCO running at 14 MHz	1/
3.0 EMI Current consumption with all poripheral clocks disabled and HERCO running at 11 MHz	15
3.10 EM1 Current consumption with all peripheral clocks disabled and HERCO running at 1.6 MHz	15
3.11 EM2 current consumption with an peripheral clocks of salide and the NCO funning at 0.0 WHZ	16
3.11 EM2 current consumption. KTC prescaled to TKT2, 32.700 KT2 EF KGO.	10
3.12. EMA current consumption.	10
3.13. EM4 current consumption.	17
3.14. Typical Low-Level Output Current, 2V Supply Voltage	21
3.15. Typical High-Level Output Current, 2V Supply Voltage	. 22
3.16. Typical Low-Level Output Current, 3V Supply Voltage	23
3.17. Typical High-Level Output Current, 3V Supply Voltage	. 24
3.18. Typical Low-Level Output Current, 3.8V Supply Voltage	25
3.19. Typical High-Level Output Current, 3.8V Supply Voltage	26
3.20. Calibrated LFRCO Frequency vs Temperature and Supply Voltage	28
3.21. Calibrated HFRCO 1 MHz Band Frequency vs Supply Voltage and Temperature	29
3.22. Calibrated HFRCO 7 MHz Band Frequency vs Supply Voltage and Temperature	30
3.23. Calibrated HFRCO 11 MHz Band Frequency vs Supply Voltage and Temperature	. 30
3.24. Calibrated HFRCO 14 MHz Band Frequency vs Supply Voltage and Temperature	30
3.25. Calibrated HFRCO 21 MHz Band Frequency vs Supply Voltage and Temperature	31
3.26. Integral Non-Linearity (INL)	37
3.27. Differential Non-Linearity (DNL)	37
3.28. ADC Frequency Spectrum, Vdd = 3V, Temp = 25°C	38
3.29. ADC Integral Linearity Error vs Code, Vdd = 3V, Temp = 25°C	39
3.30. ADC Differential Linearity Error vs Code, Vdd = 3V, Temp = 25°C	40
3.31. ADC Absolute Offset, Common Mode = Vdd /2	41
3.32. ADC Dynamic Performance vs Temperature for all ADC References, Vdd = 3V	41
3.33. ADC Temperature sensor readout	42
3.34. IDAC Source Current as a function of voltage on IDAC_OUT	. 45
3.35. IDAC Sink Current as a function of voltage from IDAC_OUT	. 46
3.36. IDAC linearity	46
3.37. ACMP Characteristics, Vdd = 3V, Temp = 25°C, FULLBIAS = 0, HALFBIAS = 1	48
4.1. EFM32HG309 Pinout (top view, not to scale)	52
4.2. QFN24	56
5.1. QFN24 PCB Land Pattern	58
5.2. QFN24 PCB Solder Mask	59
5.3. QFN24 PCB Stencil Design	60
6.1. Example Chip Marking (top view)	61